

SANYO Semiconductors DATA SHEET

LV5103LP — Cell Phone Power Supply IC

Overview

The LV5103LP is a cell phone power supply IC.

Functions

- Single step-down DC-DC converter channel
- Eight series regulator channels
- Built-in thermal shutdown circuit

Features

- Low power dissipation
- Built-in shorting protection circuit

Specifications

Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Maximum supply voltage	V _{CC} max		6	٧
Allowable power dissipation	Pd max	Mounted on a circuit board.*	1100	mW
Operating temperature	Topr		-30 to +75	°C
Storage temperature	Tstg		-40 to +125	°C

^{*} Specified circuit board : 40×50×0.8mm³ : 4-layer (2S2P) glass epoxy printed circuit board

Operating Conditions at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	v _{CC}		3.2 to 4.5	V

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Electrical Characteristics

Ta = 25°C, VBAT = 3.7V, VBATL = 2.4V, unless otherwise specified.

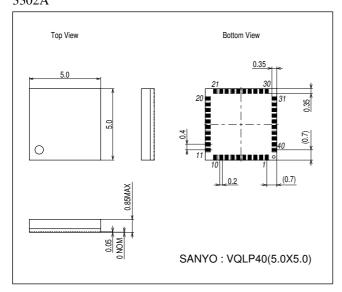
Parameter	Symbol	Conditions		Ratings		Unit
	- Cymbol	min		min typ ma		Onit
[Analog block] Current drain	<u> </u>	T		_		
Current drain 1	I _{CC} 1	With LD01 and VBATDET operating		8	16	μА
Current drain 2	I _{CC} 2	With LD01, LD02. LD05, LD06, LD07, and LD08 operating. PS mode		50	75	μА
Current drain 3	ICC3	With all LD0n channels operating, DC-DC operation		6	10	mA
[Switching Regulator Block] DC	C/DC1		•	-		
Output voltage 1	V _{OSW} 1	I _O = 500mA	2.25	2.4	2.55	٧
Output current	I _{SW} 1		800			mA
Efficiency 1	EF1	I _O = 150mA		86		%
Efficiency 2	EF2	I _O = 500mA		79		%
Oscillator frequency	Fosc1		1	1.2	1.4	MHz
LDO1			<u> </u>	<u> </u>		
Output voltage	V _{OR} 1	I _O = 10mA	1.47	1.5	1.53	V
Output current	I _M 1		30			mA
Load regulation	V _L 1	I _O = 1 to 30mA		10	75	mV
Line regulation	V _R 1	VBAT = 3.1 to 4.5V, I _O = 20mA		10	60	mV
Output voltage temperature coefficient	ΔVT1	Ta = -30 to 75°C, $I_O = 10$ mA		±100		ppm/°C
Ripple rejection ratio	V _{RL} 1	I _O = 10mA, VRR = -20dBV, fRR = 120Hz		65		dB
Output noise voltage	V _{ON} 1	I _O = 10mA, 10Hz < f < 100kHz		60		μVrms
LDO2			li-	<u> </u>		
Output voltage	V _{OR} 2	I _O = 30mA	2.79	2.85	2.91	V
Output current	I _M 2		200			mA
Load regulation	V _L 2	I _O = 1 to 200mA		20	75	mV
Line regulation	V _R 2	VBAT = 3.1 to 4.5V, I _O = 130mA		10	60	mV
Output voltage temperature coefficient	ΔVT2	Ta = -30 to 75°C, I _O = 30mA		±100		ppm/°C
Ripple rejection ratio	V _{RL} 2	I _O = 30mA, VRR = -20dBV, fRR = 120Hz		65		dB
Output noise voltage	V _{ON} 2	I _O = 30mA, 10Hz < f < 100kHz		50		μVrms
LDO2 PS MODE		1 -				
Output voltage	V _{OR} 2P	I _O = 30mA	2.76	2.85	2.94	V
Output current	I _M 2P		200			mA
Load regulation	V _L 2P	I _O = 1 to 200mA		20	75	mV
Line regulation	V _R 2P	VBAT = 3.1 to 4.5V, I _O = 130mA		10	60	mV
Output voltage temperature coefficient	ΔVT2P	Ta = -30 to 75°C, $I_O = 30mA$		±100		ppm/°C
Ripple rejection ratio	V _{RL} 2P	I _O = 30mA, VRR = -20dBV, fRR = 120Hz		60		dB
Output noise voltage	V _{ON} 2P	I _O = 30mA, 10Hz < f < 100kHz		60		μVrms
LDO3			· · · · · · · · · · · · · · · · · · ·			-
Output voltage	V _{OR} 3	I _O = 30mA	2.79	2.85	2.91	V
Output current	I _M 3		150			mA
Load regulation	V _L 3	I _O = 1 to 150mA		20	75	mV
Line regulation	V _R 3	VBAT = 3.1 to 4.5V, I _O = 100mA		10	60	mV
Output voltage temperature coefficient	ΔVΤ3	Ta = -30 to 75°C, I _O = 30mA		±100		ppm/°C
Ripple rejection ratio	V _{RL} 3	I _O = 30mA, VRR = -20dBV, fRR = 120Hz		65		dB
Output noise voltage	V _{ON} 3	I _O = 30mA, 10Hz < f < 100kHz		50		μVrms
LDO3B SW	, 5,,	- 1 -	i I			1
Switch on-resistance	RSW3	I _O = 50mA, SWCTL : HIGH		1.5	2.5	Ω
Switch leakage current	ISW3	SWCTL:LOW		0	3	μА

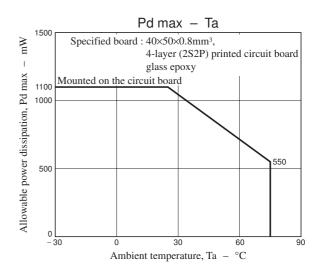
Parameter Symbol Co		Conditions			Ratings	
Farameter	Symbol	Conditions	min	typ	max	Unit
LDO4		T. 22.	1	1		l
Output voltage 1	V _{OR} 41	I _O = 30mA	3.03	3.1	3.17	V
Output voltage 2	V _{OR} 42	I _O = 200mA	3	3.1	3.2	V
Output current 1	I _M 41		450			mA
Output current 2	I _M 42	VBAT = 3.4V, V _{OUT} ≥ 3V	300			mA
Load regulation 1	V _L 4	I _O = 1 to 300mA		30	100	mV
Load regulation 2	V _L 4L	VBAT = 3.4V, I _O = 1 to 250mA		50	100	mV
Line regulation 1	V _R 4	VBAT = 3.4 to 4.5V, I _O = 200mA		10	60	mV
Output voltage temperature coefficient	ΔVT4	Ta = -30 to 75°C, I _O = 30mA		±100		ppm/°
Ripple rejection ratio	V _{RL} 4	$I_O = 30$ mA, $VRR = -20$ dBV, $fRR = 120$ Hz		65		dB
Output noise voltage	V _{ON} 4	I _O = 30mA, 10Hz < f < 100kHz		50		μVrm
LDO5						
Output voltage	V _{OR} 5	I _O = 30mA	3.23	3.3	3.37	V
Output current 1	I _M 51		150			mA
Output current 2	I _M 52	$VBAT = 3.4V, V_{OUT} \ge 3V$	150			mA
Load regulation 1	V _L 5	I _O = 1 to 150mA		75	150	mV
Load regulation 2	V _L 5L	VBAT = 3.4V, I _O = 1 to 50mA		75	150	mV
Line regulation 1	V _R 5	VBAT = 3.4 to 4.5V, I _O = 100mA		10	60	mV
Output voltage temperature coefficient	ΔVT5	Ta = -30 to 75°C, I _O = 30mA		±100		ppm/°
Ripple rejection ratio	V _{RL} 5	I _O = 30mA, VRR = -20dBV, fRR = 120Hz		65		dB
Output noise voltage	V _{ON} 5	I _O = 30mA, 10Hz < f < 100kHz		50		μVrm
LDO5 PS MODE		1 - 5	I I			
Output voltage	V _{OR} 5P	I _O = 30mA	3.2	3.3	3.4	V
Output current	I _M 5P		150			mA
Load regulation 1	V _L 5P1	I _O = 1 to 150mA		75	150	mV
Load regulation 2	V _I 5P2	VBAT = 3.4V, I _O = 1 to 50mA		75	150	mV
Line regulation 1	V _R 5P	VBAT = 3.4 to 4.5V, I _O = 100mA		10	60	mV
Output voltage temperature coefficient	ΔVT5P	Ta = -30 to 75°C, I _O = 30mA		±100		ppm/°
Ripple rejection ratio	V _{RL} 5P	I _O = 30mA, VRR = -20dBV, fRR = 120Hz		60		dB
Output noise voltage	V _{ON} 5P	I _O = 30mA, 10Hz < f < 100kHz		60		μVrm
LDO6	- I	1 - 5	I I			
Output voltage	V _{OR} 6	I _O = 30mA	1.47	1.5	1.53	V
Output current	I _M 6		200			mA
Load regulation	V _L 6	I _O = 1 to 200mA		20	75	mV
Line regulation 1	V _R 6	VBAT = 3.1 to 4.5V, I _O = 130mA		10	60	mV
Output voltage temperature coefficient	ΔVT6	Ta = -30 to 75°C, I _O = 30mA		±100		ppm/°
Ripple rejection ratio	V _{RL} 6	I _O = 30mA, VRR = -20dBV, fRR = 120Hz		65		dB
Output noise voltage	V _{ON} 6	I _O = 30mA, 10Hz < f < 100kHz		50		μVrm
LDO6 PS MODE	•	•		<u>'</u>		•
Output voltage	V _{OR} 6P	I _O = 30mA	1.45	1.5	1.55	V
Output current	I _M 6P		10			mA
Load regulation	V _L 6P	I _O = 1 to 10mA		10	75	mV
Line regulation 1	V _R 6P	VBAT = 3.1 to 4.5V, I _O = 10mA		10	60	mV
Output voltage temperature coefficient	ΔVT6P	Ta = -30 to 75°C, I _O = 30mA		±100		ppm/°
Ripple rejection ratio	V _{RL} 6P	I _O = 30mA, VRR = -20dBV, fRR = 120Hz		60		dB
Output noise voltage	V _{ON} 6P	I _O = 30mA, 10Hz < f < 100kHz		60		μVrm

Daremeter	C. mb al	Conditions		Ratings		فأحدا ا
Parameter	Symbol	Conditions	min	typ	max	Unit
LD07		_				
Output voltage	V _{OR} 7	I _O = 30mA	1.76	1.8	1.84	٧
Output current	I _M 7		150			mA
Load regulation	V _L 7	I _O = 1 to 150mA		75	150	mV
Line regulation 1	V _R 7	VBAT = 3.1 to 4.5V, I _O = 100mA		10	60	mV
Output voltage temperature coefficient	ΔVT7	Ta = -30 to 75°C, I _O = 30mA		±100		ppm/°C
Ripple rejection ratio	V _{RL} 7	$I_O = 30$ mA, VRR = -20dBV, fRR = 120Hz		65		dB
Output noise voltage	V _{ON} 7	I _O = 30mA, 10Hz < f < 100kHz		50		μVrms
LDO7 PS MODE						
Output voltage	V _{OR} 7P	I _O = 30mA	1.74	1.8	1.86	٧
Output current	I _M 7P		10			mA
Load regulation	V _L 7P	I _O = 1 to 10mA		75	150	mV
Line regulation 1	V _R 7P	VBAT = 3.1 to 4.5V, I _O = 10mA		10	60	mV
Output voltage temperature coefficient	ΔVT7P	Ta = -30 to 75°C, I _O = 30mA		±100		ppm/°C
Ripple rejection ratio	V _{RL} 7P	I _O = 30mA, VRR = -20dBV, fRR = 120Hz		60		dB
Output noise voltage	V _{ON} 7P	I _O = 30mA, 10Hz < f < 100kHz		60		μVrms
LDO8						
Output voltage 1	V _{OR} 81	I _O = 30mA	1.17	1.2	1.23	V
Output voltage 2	V _{OR} 82	I _O = 200mA	1.13	1.2	1.27	V
Output current 1	I _M 81		500			mA
Output current 2	I _M 82	VBAT = 3.4V, V _{OUT} ≥ 1.1V	500			mA
Load regulation	V _L 8	I _O = 1 to 500mA		30	70	mV
Line regulation 1	V _R 8	VBAT = 3.1 to 4.5V, I _O = 330mA		10	60	mV
Output voltage temperature coefficient	ΔVT8	Ta = -30 to 75°C, I _O = 30mA		±100		ppm/°C
Ripple rejection ratio	V _{RL} 8	I _O = 30mA, VRR = -20dBV, fRR = 120Hz		65		dB
Output noise voltage	V _{ON} 8	I _O = 30mA, 10Hz < f < 100kHz		50		μVrms
LDO8 PS MODE		1 -	l l			
Output voltage	V _{OR} 8P	I _O = 30mA	1.16	1.2	1.24	٧
Output current	I _M 8P		10			mA
Load regulation	V _I 8P	I _O = 1 to 10mA		30	100	mV
Line regulation 1	V _R 8P	VBAT = 3.1 to 4.5V, I _O = 10mA		10	60	mV
Output voltage temperature coefficient	ΔVT8P	Ta = -30 to 75°C, I _O = 30mA		±100		ppm/°C
Ripple rejection ratio	V _{RL} 8P	I _O = 30mA, VRR = -20dBV, fRR = 120Hz		60		dB
Output noise voltage	V _{ON} 8P	I _O = 30mA, 10Hz < f < 100kHz		60		μVrms
DET24	1	1 -				
Low-level detection voltage	VDL1		2.35	2.4	2.45	٧
High-level detection voltage	VDH1		2.62	2.7	2.78	V
VBATDET	I					
Low-level detection voltage	VDL2		2.3	2.4	2.5	V
High-level detection voltage	VDH2		3.1	3.2	3.3	V
BVLT Switch	I					
BVLT switch on-resistance	RSWBV	I _O = 3mA, BVLTON : HIGH		300	400	Ω
BVLT switch leakage current	ISWBV	BVLTON: LOW		0	1	μА
Control Pins	.3	1		ŭ	•	
High level 1	VH1	RFPDN, ADPTDETIN, PWRHOLD, POWERSAVE, SWCTL, BVLTON, STCLR	1.5		VBAT	V
Low level 1	VL1	RFPDN, ADPTDETIN, PWRHOLD, POWERSAVE, SWCTL, BVLTON, STCLR	0		0.3	V
High level 2	VH2	PWRKEY	VBAT×0.8		VBAT	V
Low level 2	VL2	PWRKEY	0		VBAT×0.2	V

Package Dimensions

unit: mm (typ) 3302A





Control Pin Functions

Power Supply Control

RFPDN	ADPTDET	PWRKEY	PWRHOLD	LDO1	LDO2, 5, 6, 7, 8	LDO3, 4
Low	Low	Low	Low	On	Off	Off
Low	High			On	On	Off
Low		High		On	On	Off
Low			High	On	On	Off
High	Low	Low	Low	On	Off	Off
High	High			On	On	On
High		High		On	On	On
High			High	On	On	On

(ON/OFF1) (ON/OFF2)

PS Mode

PWRSAVE	Mode
Low	PS mode
High	Normal mode

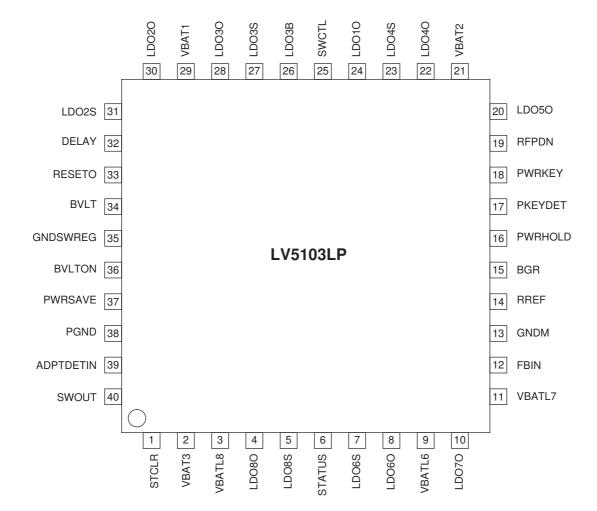
LDO3 Output Switch

SWCTL	Mode
Low	Switch off
High	Switch on

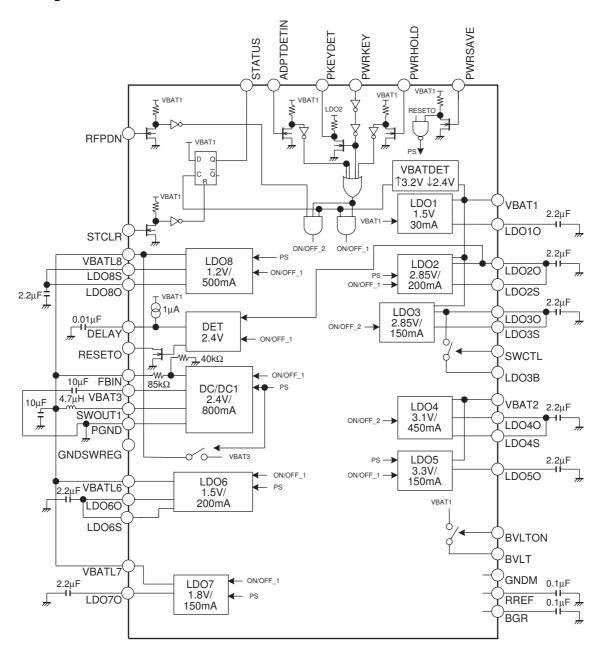
BVLT Output

BVLTON	Mode
Low	Switch off
High	Switch on

Pin Assignment



Block Diagram



The three power supply pins VBAT1, VBAT2, and VBAT3 must be shorted together externally. The three ground pins GNDM, PGND, and GNDSWREG must be shorted together externally and must always be at a potential that is the lowest potential in the system.

Equivalent Circuit Block Diagram

Pin No.	Pin	Functions	Equivalent Circuit
1	STCLR	Input pins	
16	PWRHOLD		VBAT1 O
19	RFPDN		11105
37	PWRSAVE		★ 1MΩ §
39	ADPTDETIN		
			Corresponding pin ———————————————————————————————————
			18kΩ
			A
			GNDM ○
29	VBAT1	Power supply pins	VBAT* O
21	VBAT2		0
2	VBAT3		
			<u> </u>
			A
			CNIDMO
			GNDM ○
3	VBATL8	VBATL pins	1/54-7-5
9	VBATL6	The M1 transistor is only present in the	VBAT3 VBAT1 ○
11	VBATL7	VBATL8 circuit.	VBATTO
			<u></u>
			M1/
			VBATL* O
			VBATE O
			★
			T
			GNDM O
4	LDO8O	LDO output pins	
5	LDO8S	The LDO*O pins for LDO1, LDO5, and	→
7	LDO6S	LDO7 are shorted internally in the IC to	
8	LDO6O	the corresponding LDO*S pin.	
10	LDO7O		
20	LDO5O		○ LDO*O
22	LDO4O		
23	LDO4S		_ }
24	LDO10		<u></u>
27	LDO3S		
28	LDO3O		CNDM o
30	LDO2O		GNDM O-
31	LDO2S		
6	STATUS	STATUS pin	VBAT1 ○ + +
			VBATTO
			★
			<u> </u>
			STATUS O
			│
			GNDM O
			GITEIN O

Continued from preceding page. Pin No. Pin Functions Equivalent Circuit 12 FBIN Feedback resistor connection for the FBIN Oswitching regulator block 85kΩ ≥ 40kΩ ≶ GNDSWREG ○ 14 RREF RREF reference voltage -○ VBAT1 O RREF $\stackrel{>}{\geqslant} 4.8 \mathrm{M}\Omega$ **≩** 4.8MΩ - GNDM 15 BGR BGR reference voltage O RREF $1k\Omega$ -⊖ BGR –⁄w∕– 10kΩ -O GNDM 17 RKEYDET PKEYDET pin LDO2S O-- ∨BAT1 **≥** 100kΩ → PKEYDET -W---200Ω GNDM ○ 18 **PWRKEY** PWRKEY pin VBAT10 PWRKEY O $18k\Omega$ GNDM O-

Pin No.	rom preceding pa	Functions	Equivalent Circuit
25 26	SWCTL LDO3B	SWCTL pin LDO3B pin	VBAT1 O + LDO3O
20	LDOSD	LBCOB pili	ΣΑΤΤΟ Ι ξ
			18kΩ,
			SWCTL O W
			LDO3B
			OVIDM o
	DEL AV	BELAY :	GNDM O
32	DELAY	DELAY pin	VBAT1 O
			* -
			\$1kΩ 18kΩ
			DELAY O W
			<u>↓</u>
			0
33	RESET	RESET pin	→ ∨BAT1
			<u> </u>
			200Ω W- O RESET
			_
			→
			→ O GNDM
34 36	BVLT BVLTON	BVLT and BVLTON pins	VBAT1 O
00	BVETOIT		★ ★ 1MΩ ★
			18kΩ
			BVLTON O W BVLT
			↓
			OVEN O
40	CMOLIT	CWDEC as the stable of	GNDM O
40	SWOUT	SWREG output block	VBAT3 O VBAT1
			Ι 1κΩ
			SWOUT
			DOWN C
			PGND O GNDM

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